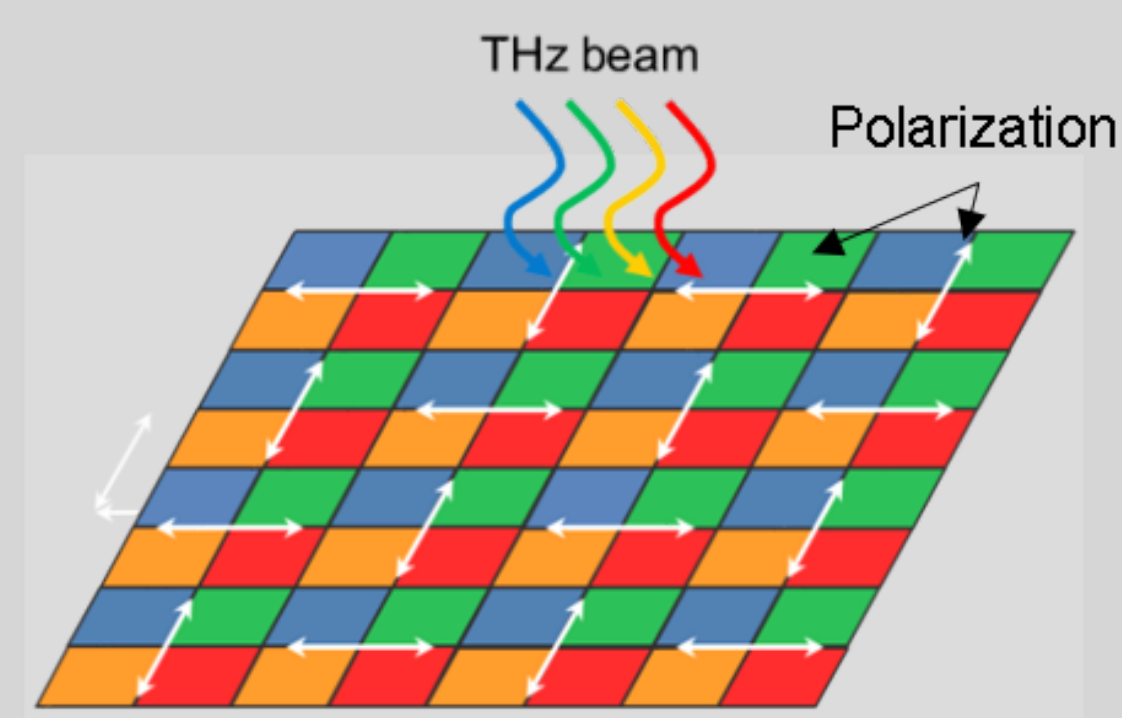


THESTRAL: A High Granularity Monolithic THz Pixel Detector

Alexander Elsenhans | Michele Caselle | Ekaterina Kunakovskaya | Christian Bohn | Ahmet Cagri Ulusoy

Goal

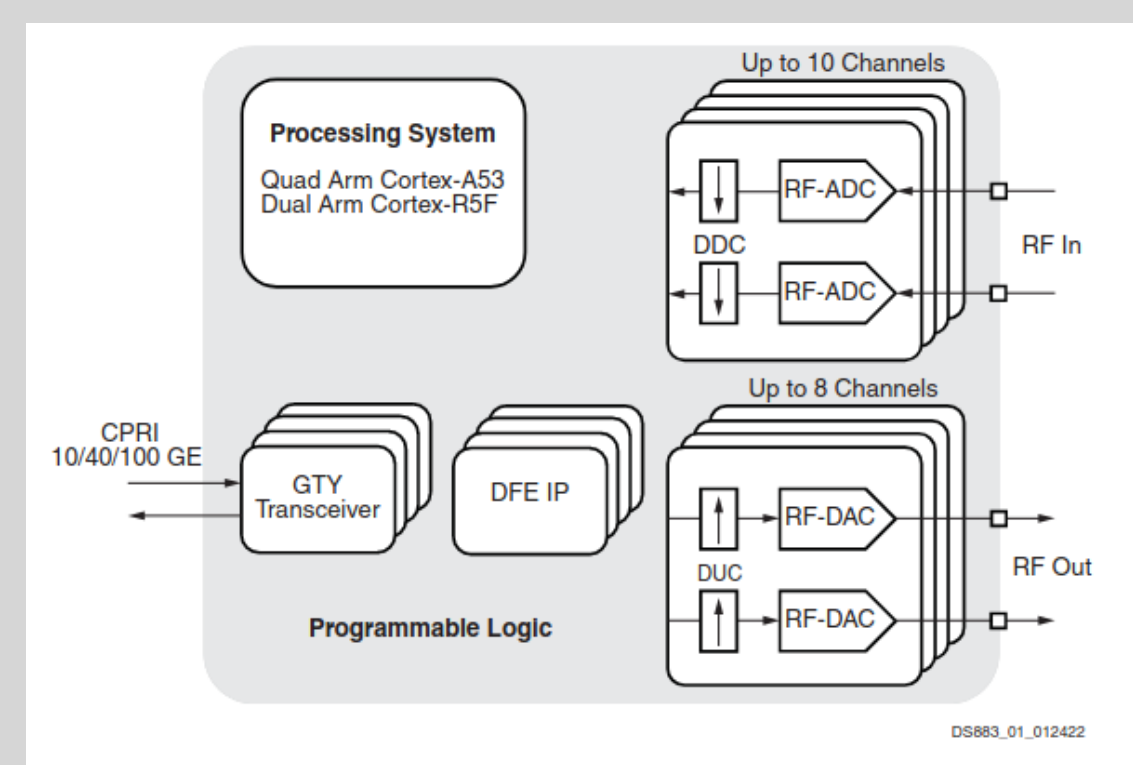


THESTRAL
(TeraHertz pixelated SpectRAL detector)

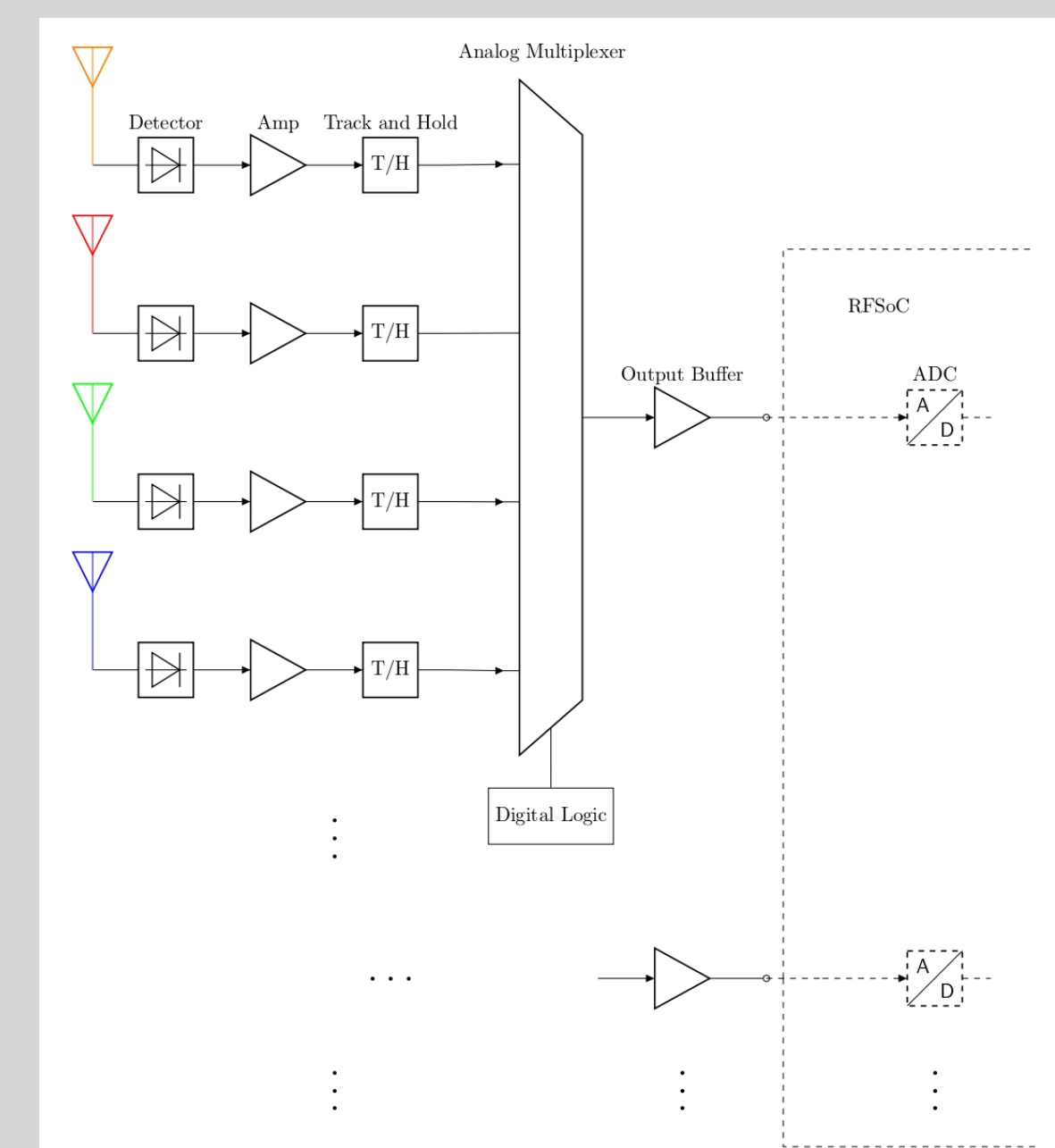
- Cutting-edge monolithic THz detector that combines: spatial, spectral, timing and polarization measurement

Principle

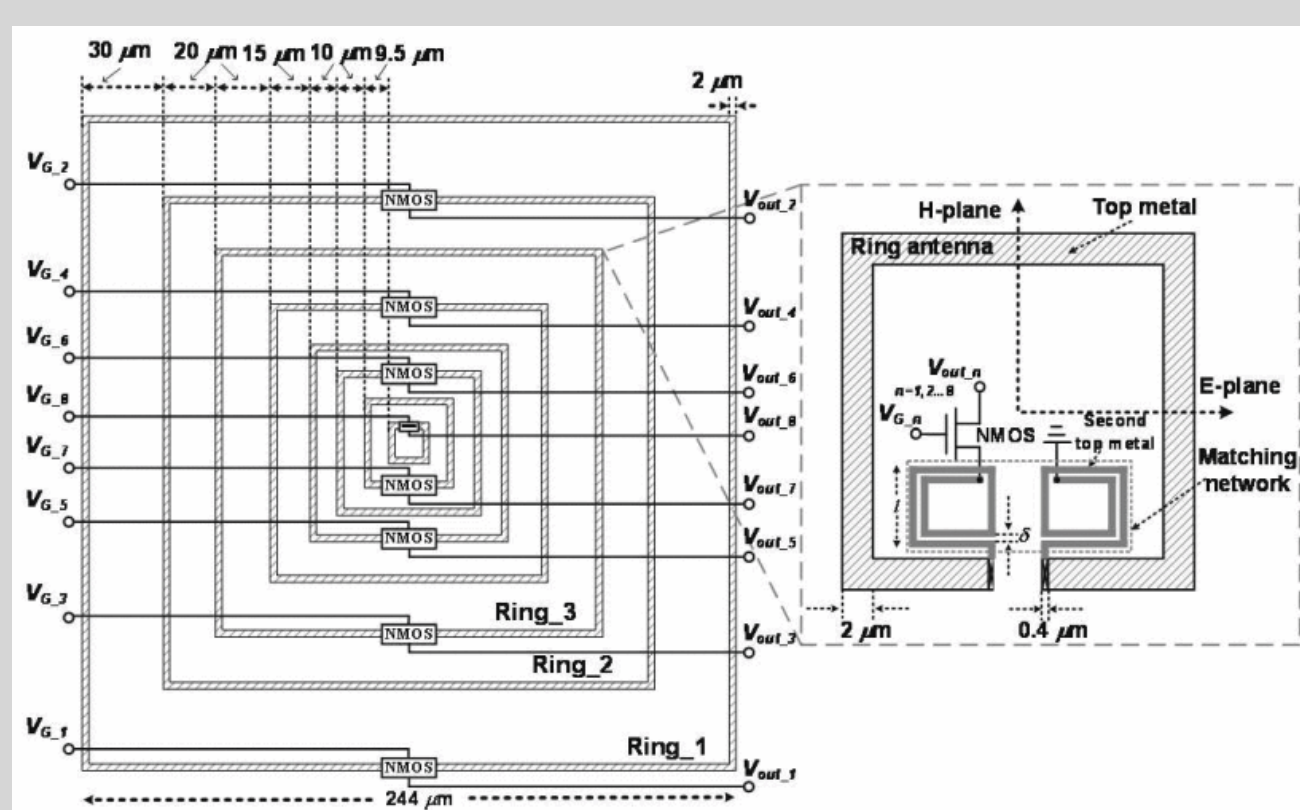
- 16 Pixel THz camera with 500 Mfps
- Each pixel contains several antennas tuned to different properties
- Readout with RFSoc from Xilinx [1]



Chip Architecture

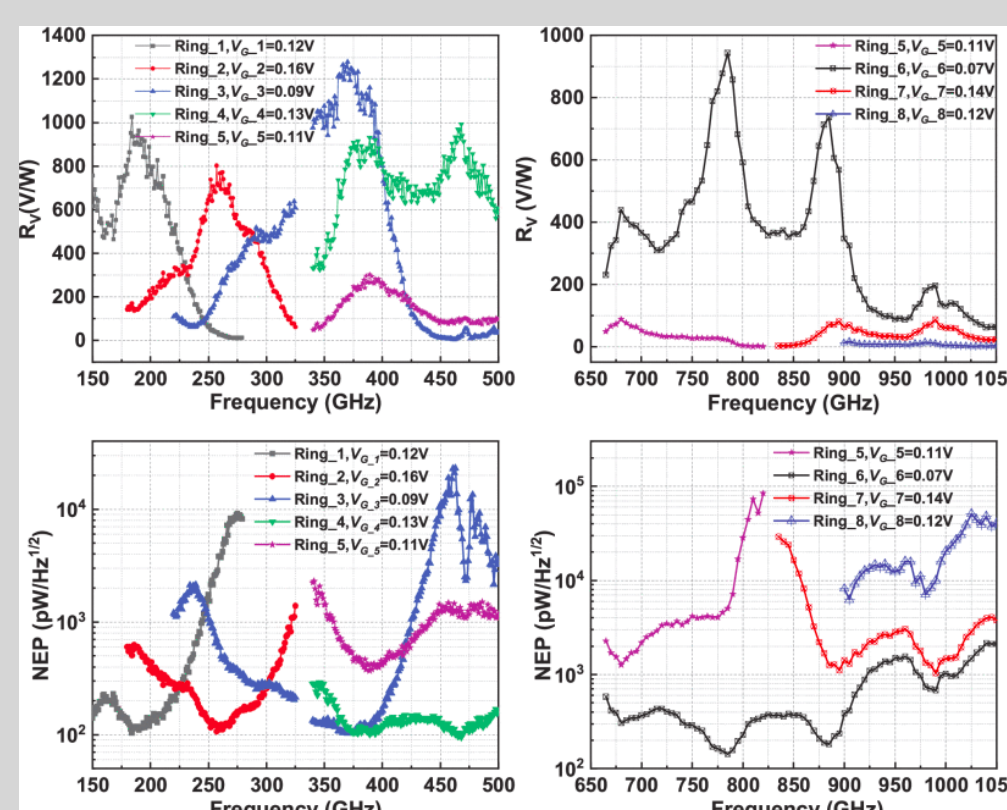


Antenna



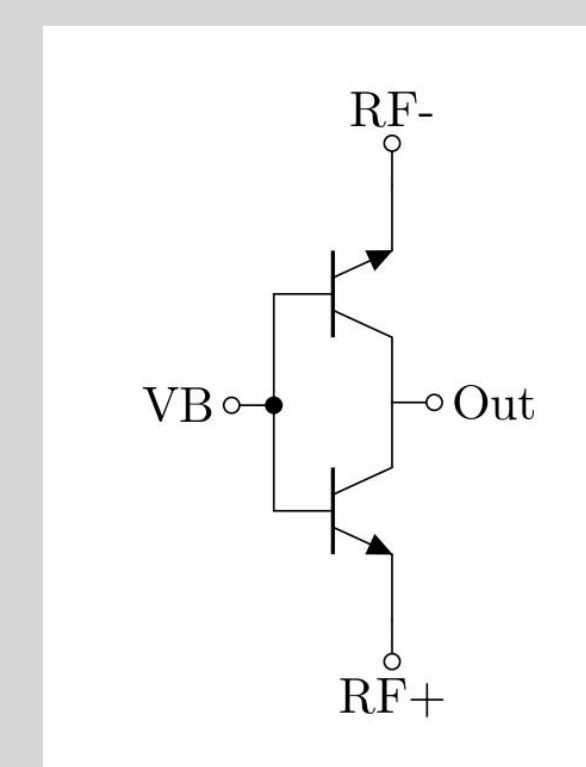
Array of ring antennas [2]

- Possible design: arrays of ring antennas tuned to different frequencies
- Polarization measurement by antenna readout with 2 differential detectors [3]
- Principle already approved in 65 nm CMOS [2]



Measured Responsivity and NEP [2]

Detector

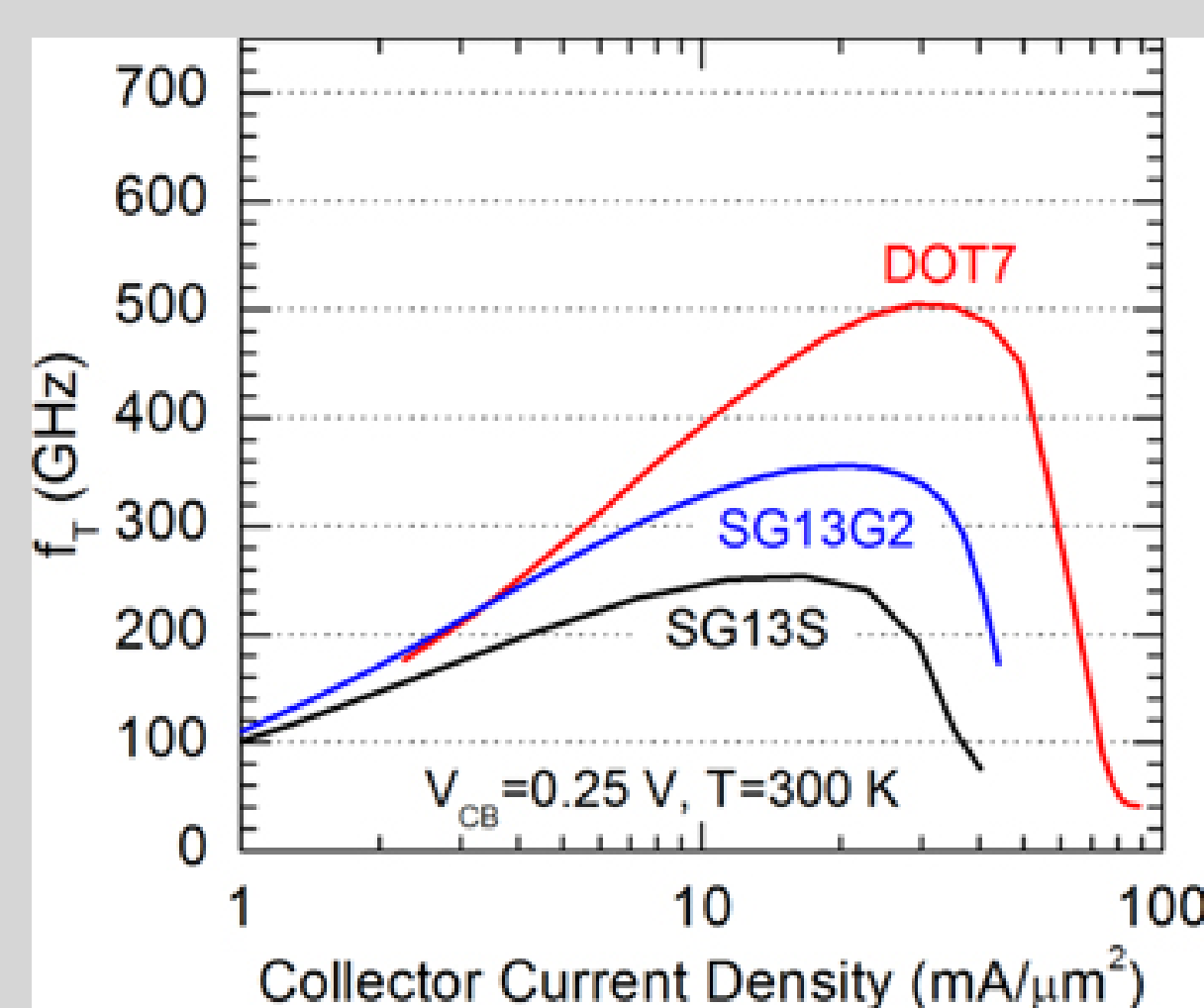


Differential Common Base detector [4]

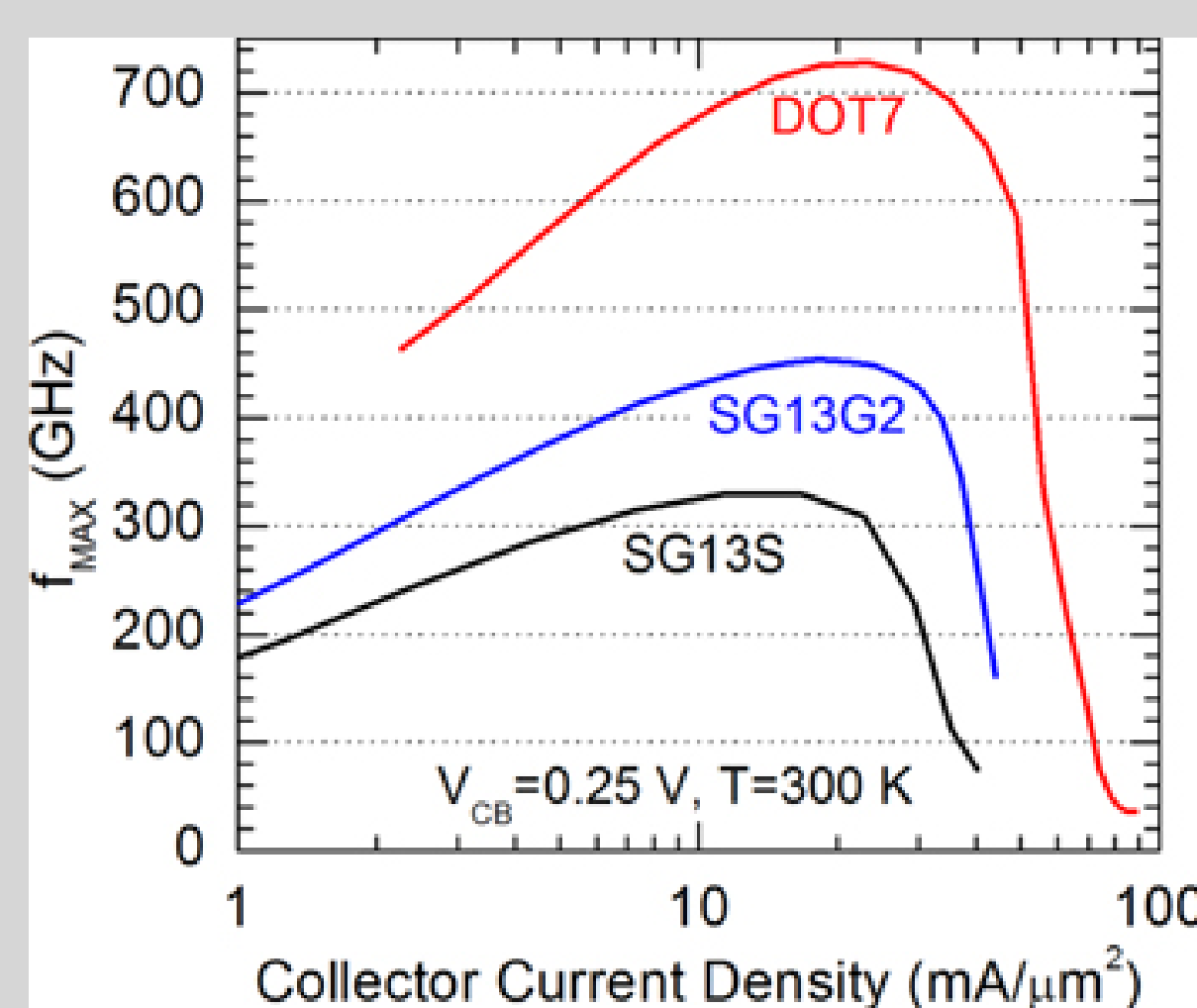
- Detector based on SG13G3 HBT with very high f_{max}
- Detection of signals > 1 THz feasible

IHP SG13G3

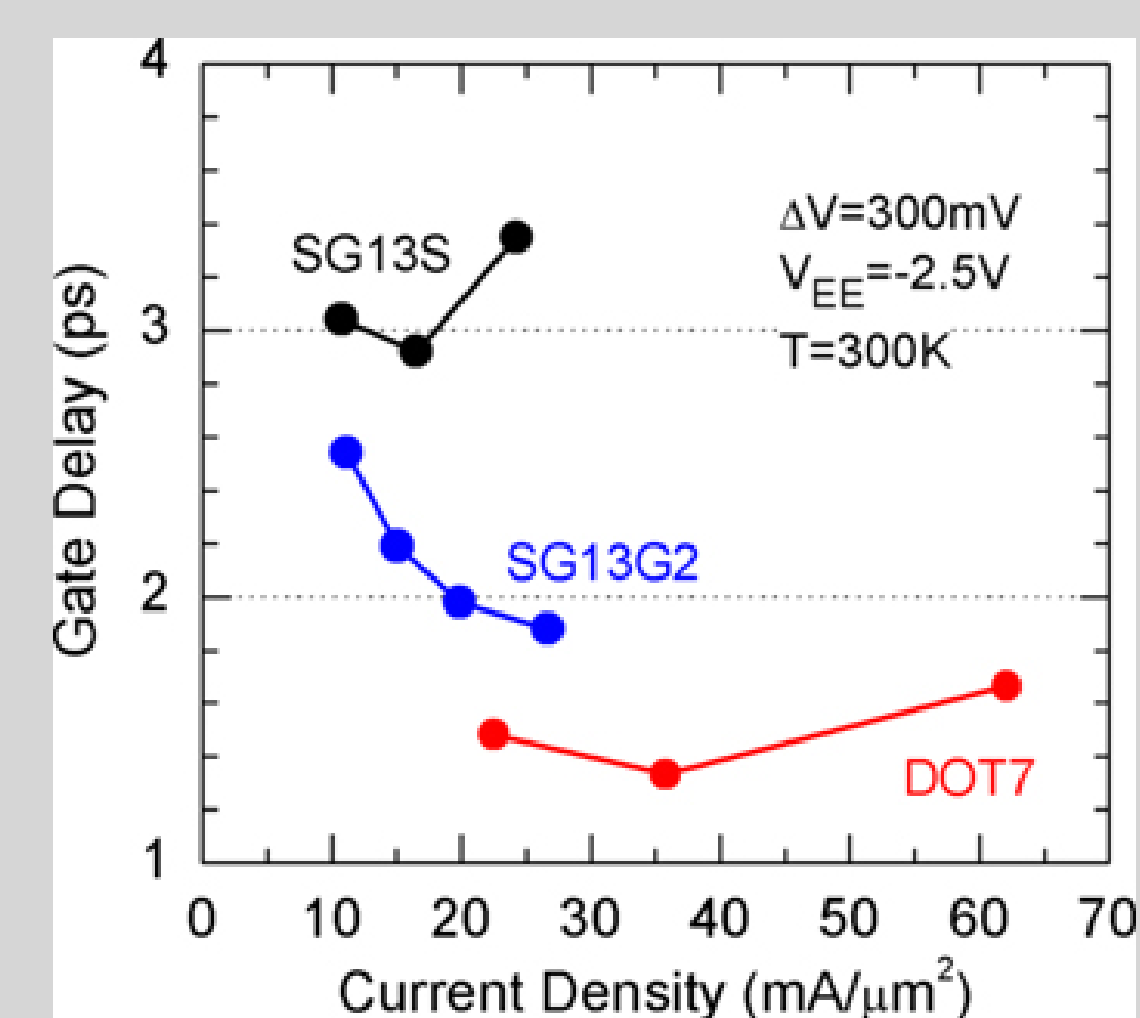
130 nm SiGe BiCMOS with extraordinary transistor performance developed in DOTSEVEN project [5]



Transit frequency f_T of HBTs (DOT7=SG13G3)



f_{max} of HBT (DOT7=SG13G3)



Gate Delay of HBT (DOT7=SG13G3)

References

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- [4] M. Andree, J. Grzyb, R. Jain, B. Heinemann and U. R. Pfeiffer, "A broadband dual-polarized terahertz direct detector in a 0.13- μm sige hbt technology," in *2019 IEEE MTT-S International Microwave Symposium (IMS)*, 2019, pp. 500–503. doi: 10.1109/MWSYM.2019.8700871.
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